TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL PLANAR TYPE

2 S C 5 0 9 4

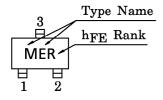
VHF~UHF BAND LOW NOISE AMPLIFIER APPLICATIONS

- Low Noise Figure, High Gain.
- NF=1.8dB, $|S_{21e}|^2 = 7.5dB$ (f=2GHz)

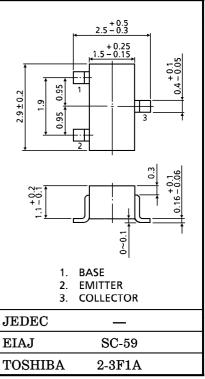
MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	v_{CBO}	20	V
Collector-Emitter Voltage	v_{CEO}	10	V
Emitter-Base Voltage	$V_{ m EBO}$	1.5	V
Base Current	$I_{\mathbf{B}}$	7	mA
Collector Current	$I_{\mathbf{C}}$	15	mA
Collector Power Dissipation	$P_{\mathbf{C}}$	150	mW
Junction Temperature	T_{j}	125	°C
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~125	°C

MARKING



Unit in mm



Weight: 0.012g

MICROWAVE CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Transition Frequency	$ m f_{T}$	$V_{CE}=6V, I_{C}=7mA$	7	10	_	GHz
Insertion Gain	$ S_{21e} ^2$ (1)	$V_{CE}=6V$, $I_{C}=7mA$, $f=1GHz$	_	13	_	dB
	$ S_{21e} ^2$ (2)	$V_{CE}=6V$, $I_{C}=7mA$, $f=2GHz$	4.5	7.5	_	ub
Noise Figure	NF (1)	$V_{CE}=6V$, $I_{C}=3mA$, $f=1GHz$	_	1.4	_	dB
	NF (2)	$V_{CE}=6V$, $I_{C}=3mA$, $f=2GHz$	_	1.8	3.0	иБ

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = 10V, I_{E} = 0$	_	_	1	μ A
Emitter Cut-off Current	I_{EBO}	$V_{EB}=1V, I_{C}=0$	_	_	1	μ A
DC Current Gain	hFE (Note 1)	$V_{CE}=6V, I_{C}=7mA$	50	_	160	
Output Capacitance	$C_{\mathbf{ob}}$	$V_{CB} = 10V, I_{E} = 0, f = 1MHz$	1	0.5	_	pF
Reverse Transfer Capacitance	$\mathrm{C_{re}}$	(Note 2)	_	0.4	0.85	рF

(Note 1) $h_{\mbox{\scriptsize FE}}$ Classification $R:50{\sim}100,~O:80{\sim}160$

(Note 2) Cre is measured by 3 terminal method with capacitance bridge.

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0.1

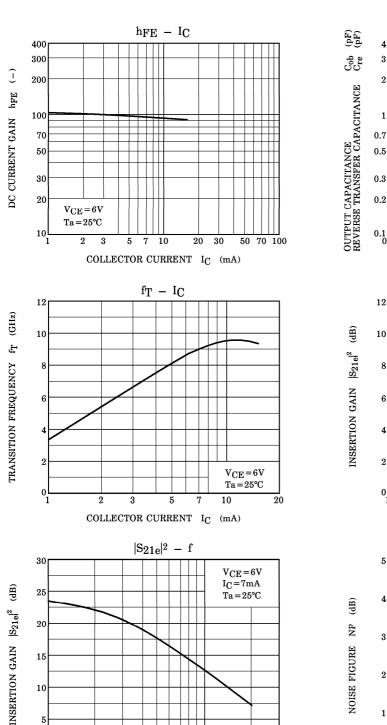
0.2

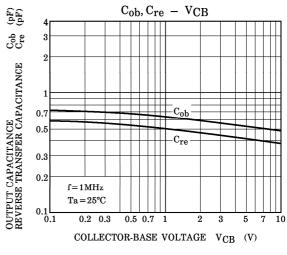
0.3

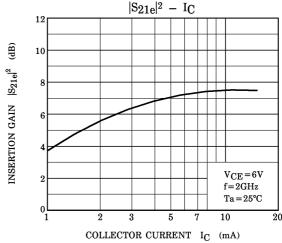
0.5 0.7

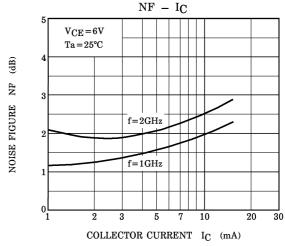
FREQUENCY f (GHz)

2

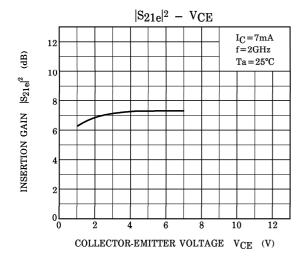


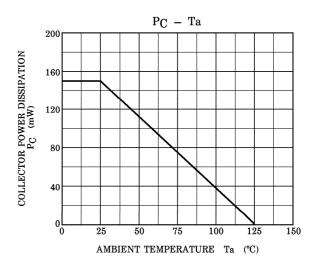






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S-Parameter $Z_O = 50\Omega$, $Ta = 25^{\circ}C$ $V_{CE} = 6V$, $I_C = 3mA$

frequency	S11		S21		S12		S22	
(MHz)	Mag.	Ang.	Mag.	Ang.	Mag.	Ang.	Mag.	Ang.
200	0.817	-25.8	7.113	150.2	0.044	71.4	0.898	-18.6
400	0.647	-46.3	6.028	129.5	0.073	61.8	0.746	-28.7
600	0.477	-61.4	5.061	113.9	0.092	57.2	0.636	-33.4
800	0.356	-71.3	4.197	102.8	0.108	55.7	0.565	-35.4
1000	0.265	-78.9	3.583	93.9	0.123	55.3	0.518	-36.8
1200	0.194	-85.6	3.135	86.7	0.137	55.7	0.486	-37.5
1400	0.136	-90.5	2.778	80.2	0.153	55.8	0.467	-38.8
1600	0.093	-97.7	2.490	74.4	0.169	55.3	0.449	-40.4
1800	0.058	-109.0	2.260	69.6	0.183	54.8	0.433	-42.6
2000	0.028	-134.7	2.089	65.2	0.199	55.2	0.418	-43.9

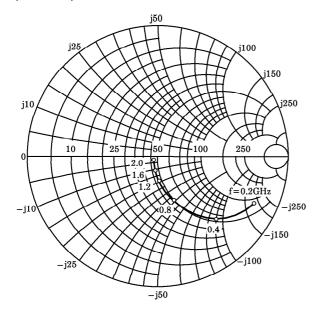
$V_{CE} = 6V$, $I_C = 7mA$

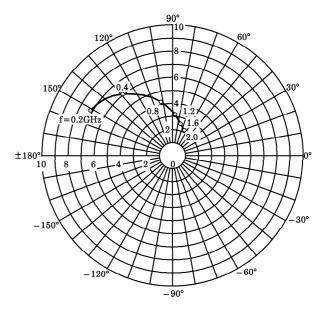
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frequency	S11		S21		S12		S22	
(MHz)	Mag.	Ang.	Mag.	Ang.	Mag.	Ang.	Mag.	Ang.
200	0.630	-39.7	12.332	138.1	0.037	68.5	0.783	-25.6
400	0.392	-64.1	8.847	114.7	0.059	64.3	0.586	-31.8
600	0.248	-78.3	6.514	101.4	0.077	64.1	0.495	-32.0
800	0.161	-87.5	5.094	92.6	0.096	64.7	0.449	-31.2
1000	0.105	-95.3	4.213	85.9	0.114	64.9	0.423	-30.5
1200	0.060	-106.3	3.589	80.3	0.133	65.0	0.412	-30.8
1400	0.028	-121.7	3.139	74.9	0.154	64.0	0.406	-32.1
1600	0.021	-158.4	2.786	70.1	0.173	62.5	0.398	-34.0
1800	0.035	171.6	2.498	66.0	0.190	61.2	0.387	-36.7
2000	0.054	144.0	2.300	62.3	0.210	60.7	0.377	-38.4

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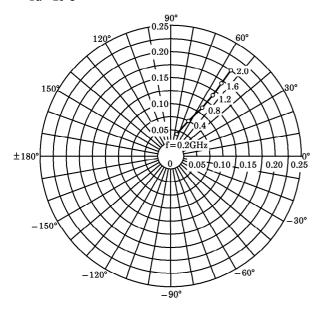
 $\begin{array}{l} S_{11e} \\ V_{CE} \!=\! 6V \\ I_{C} \!=\! 3mA \\ T_{a} \!=\! 25^{\circ}\! C \\ (UNIT:\Omega) \end{array}$







 $\begin{array}{c} S_{12e} \\ V_{CE} = 6V \\ I_{C} = 3mA \\ Ta = 25^{\circ}C \end{array}$

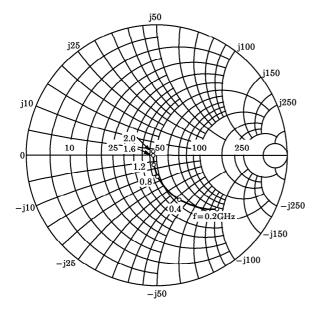


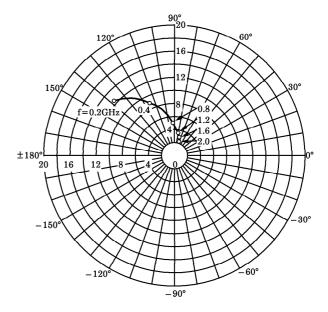
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-j50

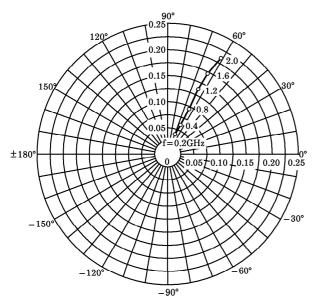
 $\begin{array}{l} S_{11e} \\ V_{CE} = 6V \\ I_{C} = 7mA \\ Ta = 25^{\circ}C \\ (UNIT:\Omega) \end{array}$

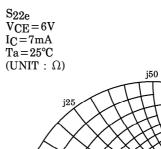


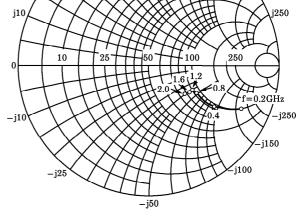












j100

j150

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